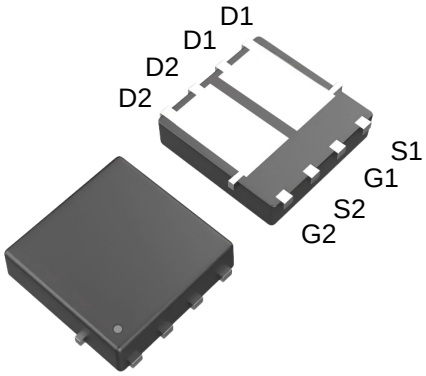
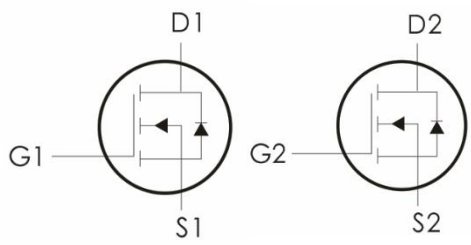
Description：

This Dual N-Channel MOSFET uses advanced trench technology and design to provide excellent $R_{DS(on)}$ with low gate charge.

It can be used in a wide variety of applications.





Features：

1) V_{DS}=30V,I_D=10A,$R_{DS(ON)}$<25mΩ @V_{GS}=10V（Typ：18mΩ）
2) Low gate charge.
3) Green device available.
4) Advanced high cell denity trench technology for ultra low $R_{DS(ON)}$.
5) Excellent package for good heat dissipation.
6) MSL3

Package Marking and Ordering Information：

Part NO.	Marking	Package	Packing
DOZ4822	4822	DFN3*3-8D	5000 pcs/Reel

Absolute Maximum Ratings：(T_c=25℃ unless otherwise noted)

Symbol	Parameter	Ratings	Units
V_{DS}	Drain-Source Voltage	30	V
V_{GS}	Gate-Source Voltage	±20	V
I_D	Continuous Drain Current[1]	10	A
	Continuous Drain Current-T_A=100℃[1]	7	
I_{DM}	Pulsed Drain Current[2]	40	
P_D	Power Dissipation	15.6	W
E_{AS}	Single pulse avalanche energy[3]	---	mJ
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55-+150	℃

Thermal Characteristics：

Symbol	Parameter	Max	Units
$R_{\theta JC}$	Thermal Resistance,Junction to Case	8	℃/W

Electrical Characteristics: (T_c=25℃ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
Off Characteristics						
BV_{DSS}	Drain-Sourtce Breakdown Voltage	V_{GS}=0V,I_D=250μA	30	---	---	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{GS}=0V, V_{DS}=30V	---	---	1	μA
I_{GSS}	Gate-Source Leakage Current	V_{GS}=±20V, V_{DS}=0A	---	---	±100	nA
On Characteristics						
$V_{GS(th)}$	Gate-Source Threshold Voltage	V_{GS}=V_{DS}, I_D=250μA	1	1.5	2	V
$R_{DS(ON)}$	Drain-Source On Resistance[4]	V_{GS}=10V,I_D=8A	---	18	25	mΩ
		V_{GS}=4.5V,I_D=4A	---	25	30	
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS}=15V, V_{GS}=0V, f=1MHz	---	450	---	pF
C_{oss}	Output Capacitance		---	50	--	
C_{rss}	Reverse Transfer Capacitance		---	38	---	
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	V_{DS}=15V, I_D=1A, R_G=3.3Ω ,V_{GS}=4.5V	---	2.6	---	ns
t_r	Rise Time		---	8.2	---	ns
$t_{d(off)}$	Turn-Off Delay Time		---	15	---	ns
t_f	Fall Time		---	4.1	---	ns
Q_g	Total Gate Charge	V_{GS}=15V, V_{DS}=4.5V, I_D=4A	---	5.2	---	nC
Q_{gs}	Gate-Source Charge		---	0.8	---	nC
Q_{gd}	Gate-Drain “Miller” Charge		---	1.5	---	nC
Drain-Source Diode Characteristics						
V_{SD}	Diode Forward Voltage	V_{GS}=0V, I_{SD}=4A	---	---	1.2	V
I_S	Continuous Drain Curren	V_D=V_G=0V	---	---	10	A
I_{SM}	Pulsed Drain Current		---	---	40	A

Notes:

1. Computed continuous current assumes the condition of $T_{j,Max}$ while the actual continuous current depends on the thermal & electro-mechanical application board design
2. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature
3. EAS condition : TJ=25℃,VDD=15V,V_G=10V,L=0.5mH
4. Pulse Test: Pulse Width≤300μs, Duty Cycle≤0.5%

Typical Characteristics: (T_c=25℃ unless otherwise noted)

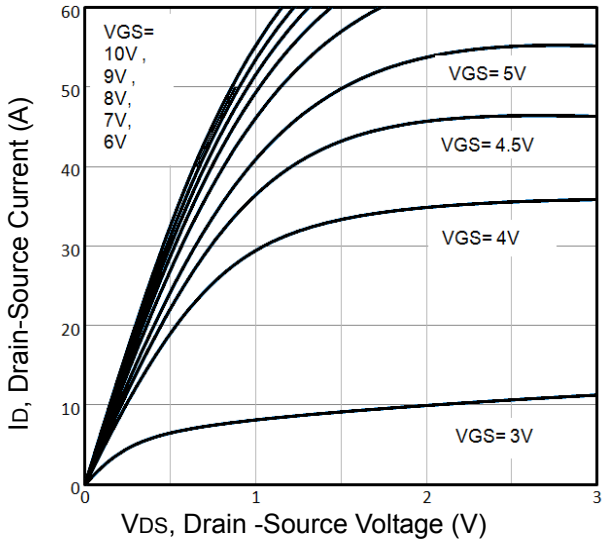


Fig1. Typical Output Characteristics

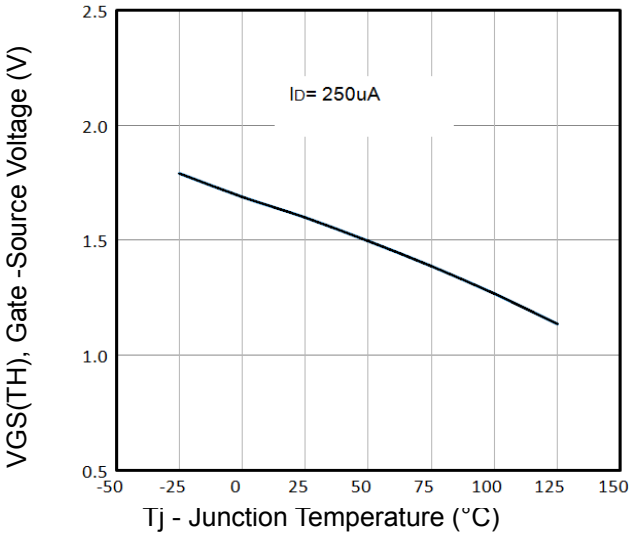


Fig2. VGS(TH) Voltage Vs. Temperature

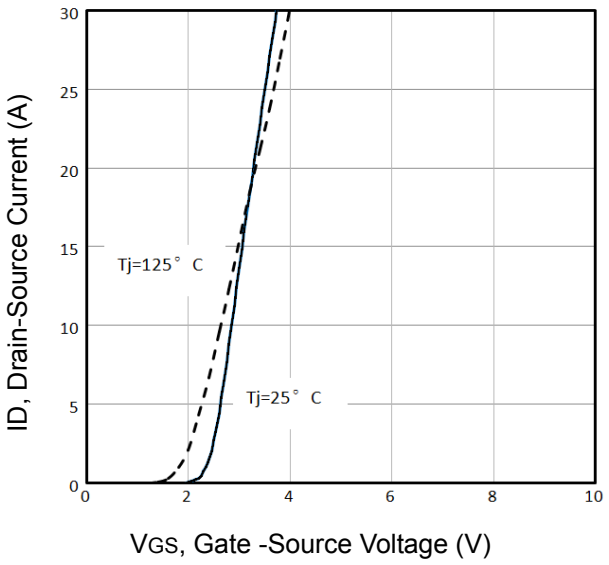


Fig3. Typical Transfer Characteristics

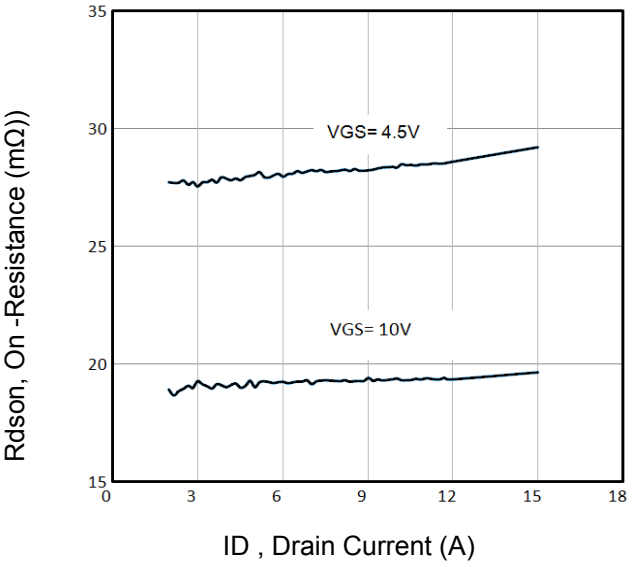


Fig4. On-Resistance vs. Drain Current and Gate

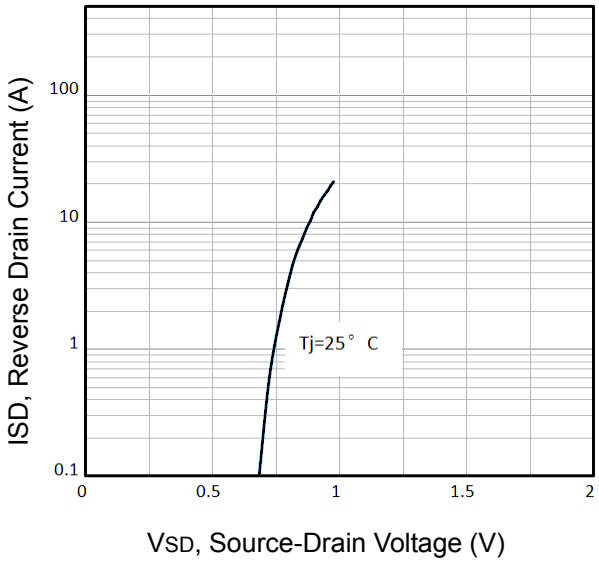


Fig5. Typical Source-Drain Diode Forward Voltage

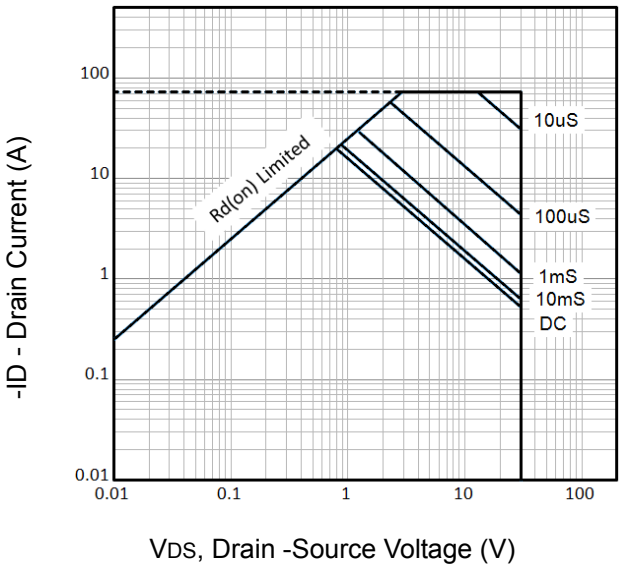


Fig6. Maximum Safe Operating Area

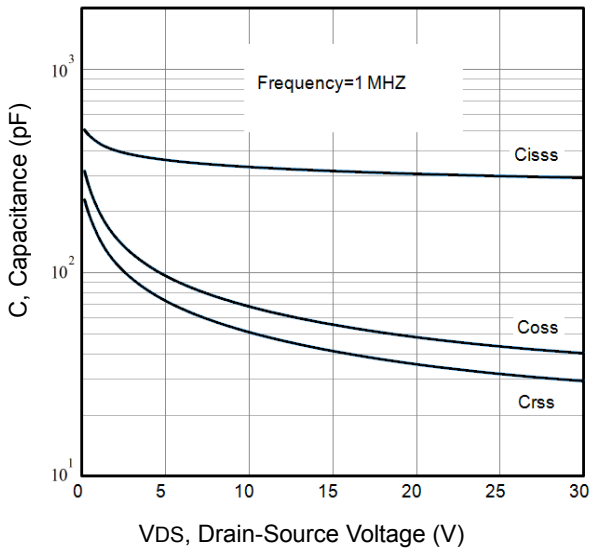


Fig7. Typical Capacitance Vs. Drain-Source Voltage

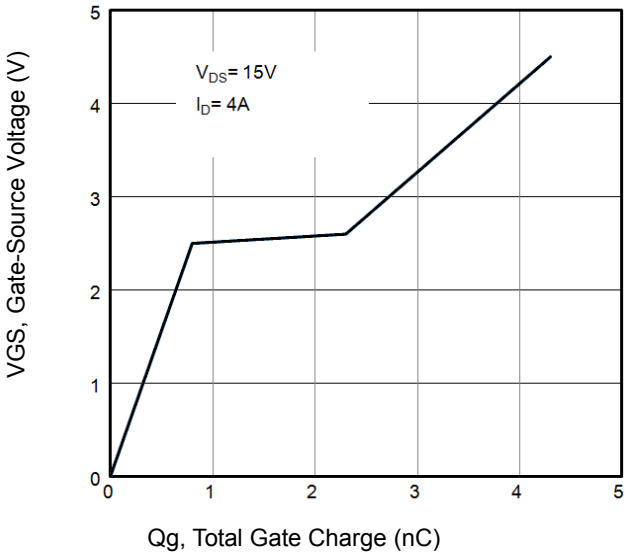


Fig8. Typical Gate Charge Vs. Gate-Source Voltage

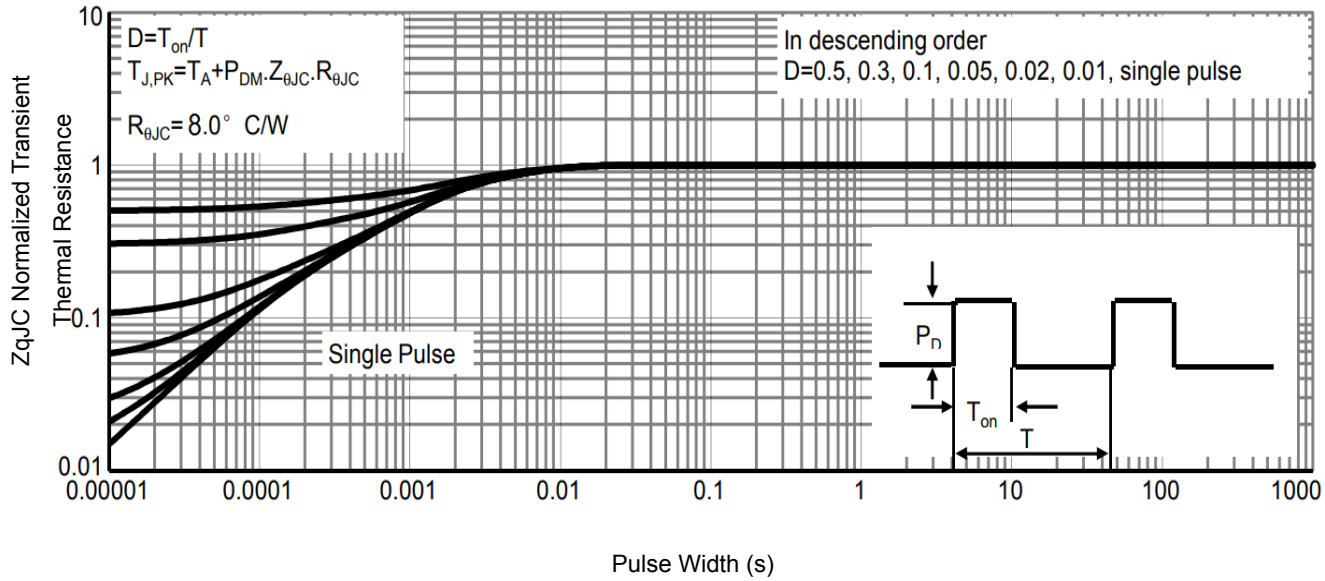


Fig9. Normalized Maximum Transient Thermal Impedance

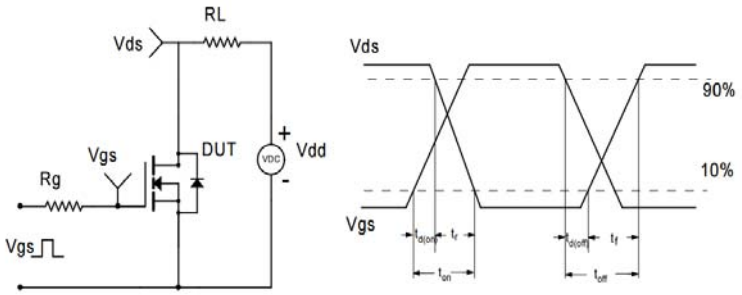
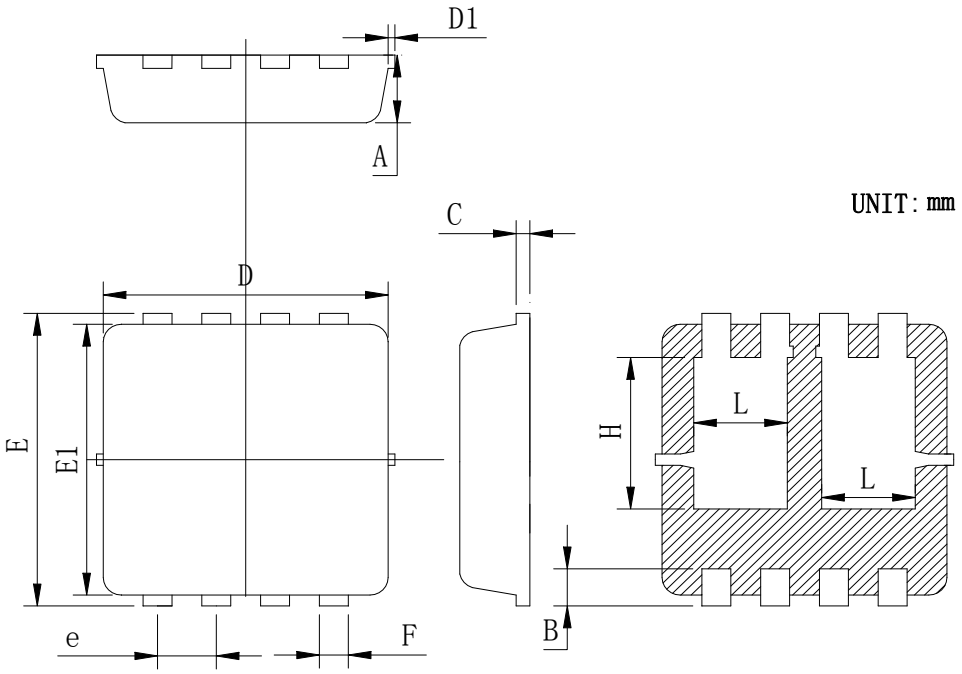


Fig10. Switching Time Test Circuit and waveforms

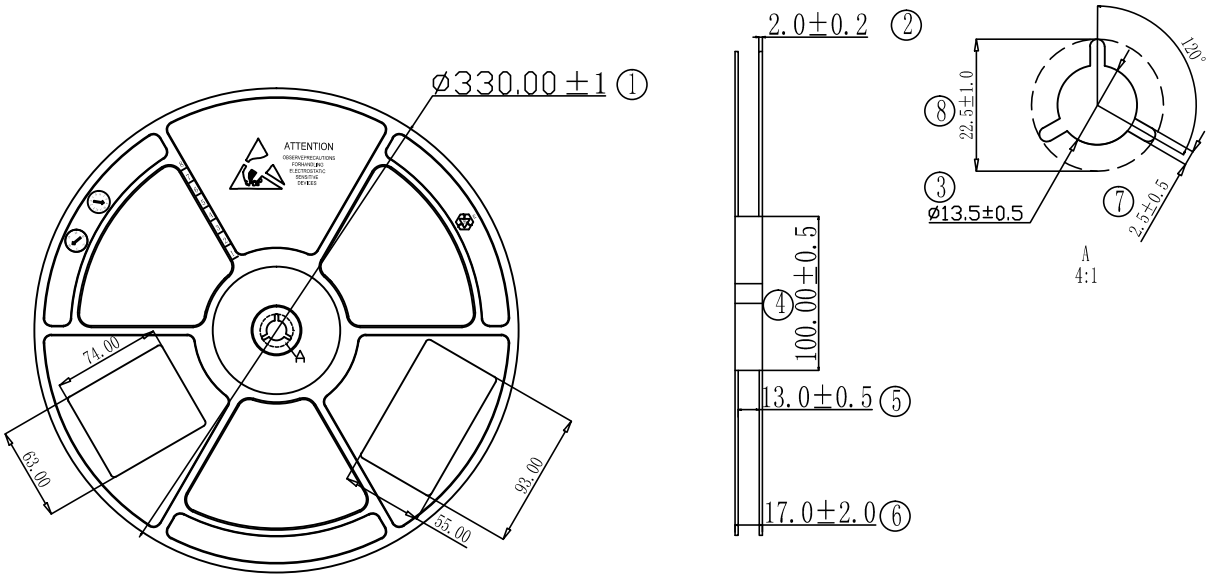
DFN3X3-8D Package Outline Data



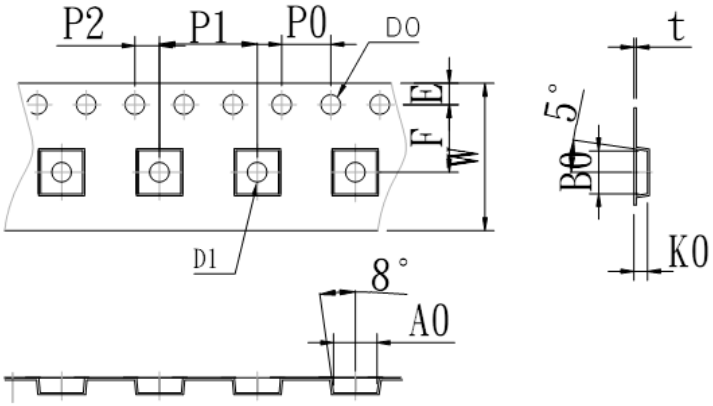
Symbol	Min	Typ	Max
A	0.725	0.775	0.825
B	0.28	0.38	0.48
C	0.13	0.15	0.20
D	3.05	3.15	3.25
D1			0.10
E	3.25	3.35	3.45
E1	3.0	3.1	3.2
e	0.60	0.65	0.70
F	0.27	0.32	0.37
H	1.63	1.73	1.83
L	0.93	1.03	1.13

Tape & Reel Information

Dimensions in mm



Symbol	A0	B0	K0	D0	D1	P0	P1	10*P0
Spec	3.55±0.10	3.45±0.10	1.13±0.10	1.55±0.10	1.55±0.10	4.00±0.10	8.00±0.10	40.0±0.10
Symbol	W	E	F	P2	t			
Spec	12.00±0.10	1.75±0.10	5.50±0.10	2.00±0.10	0.20±0.05			



Pulling direction

Marking Information：

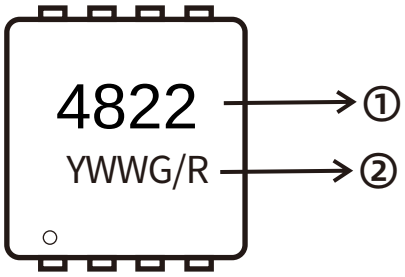
①. Part NO.

②. Date Code(YWWG / R)

Y : Year Code , last digit of the year

WW : Week Code(01-53)

G/R : G(Green) /R(Lead Free)



Previous Version

Version	Date	Subjects (major changes since last revision)
1.0	2021-04-13	Release of final version

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